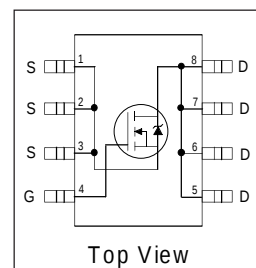


- N-Channel Application-Specific MOSFETs
- Ideal for CPU Core DC-DC Converters
- New **CopperStrap™** Interconnect for Lower Electrical and Thermal Resistance
- Low Conduction Losses
- Low Switching Losses
- Minimizes Parallel MOSFETs for high current applications

HEXFET® Chipset for DC-DC Converters



Description

These new devices employ advanced HEXFET® Power MOSFET technology to achieve an unprecedented balance of on-resistance and gate charge. The reduced conduction and switching losses make them ideal for high efficiency DC-DC converters that power the latest generation of mobile microprocessors.

The IRF7809/IRF7811 employs a new **CopperStrap™** interconnect technology pioneered by International Rectifier to dramatically improve the electrical & thermal resistance contribution of the package. The new **CopperStrap** SO-8 power MOSFETs are capable of current ratings over 17A and power dissipation of 3.5W @ 25°C ambient conditions, thereby reducing the need for paralleled devices, improving efficiency and reliability and reducing board space.

DEVICE RATINGS

	IRF7809	IRF7811
V_{DS}	30V	28V
$R_{DS(on)}$	7.5 mΩ	11 mΩ
Q_G	77.5 nC	23 nC
Q_{sw}	23.9 nC	7 nC
Q_{oss}	30 nC	31 nC

Absolute Maximum Ratings

Parameter	Symbol	IRF7809	IRF7811	Units
Drain-Source Voltage	V_{DS}	30	28	V
Gate-Source Voltage	V_{GS}	±12		
Continuous Drain or Source Current ($V_{GS} \geq 4.5V$)	I_D	17.6	14	A
		16.3	13	
Pulsed Drain Current①	I_{DM}	100	100	
Power Dissipation	P_D	3.5		W
		3.0		
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150		°C
Continuous Source Current (Body Diode)	I_S	2.5	2.5	A
Pulsed Source Current①	I_{SM}	50	50	

Thermal Resistance

Parameter		Max.	Units
Maximum Junction-to-Ambient③	$R_{\theta JA}$	35	°C/W
Maximum Junction-to-Lead	$R_{\theta JL}$	20	°C/W

IRF7809/IRF7811

International
IR Rectifier

Electrical Characteristics		IRF7809			IRF7811			Units	Conditions
Parameter		Min	Typ	Max	Min	Typ	Max		
Drain-to-Source Breakdown Voltage*	BV_{DSS}	30	–	–	28	–	–	V	$V_{GS} = 0V, I_D = 250\mu A$
Static Drain-Source on Resistance*	$R_{DS(on)}$		6	7.5		9	11	m Ω	$V_{GS} = 4.5V, I_D = 15A$ ②
Gate Threshold Voltage*	$V_{GS(th)}$	1.0			1.0			V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Drain-Source Leakage Current*	I_{DSS}			30			30	μA	$V_{DS} = 24V, V_{GS} = 0$
				150			150		$V_{DS} = 24V, V_{GS} = 0,$ $T_J = 100^\circ C$
Gate-Source Leakage Current*	I_{GSS}			± 100			± 100	nA	$V_{GS} = \pm 12V$
Total Gate Chg Cont FET*	Q_G		66.7	86.6		19	23	nC	$V_{GS}=5V, I_D=15A, V_{DS}=16V$
Total Gate Chg Sync FET*	Q_G		59.6	77.5		17	20.5		$V_{GS} = 5V, V_{DS} < 100mV$
Pre-Vth Gate-Source Charge	Q_{GS1}		14			2.7			$V_{DS} = 16V, I_D = 15A$
Post-Vth Gate-Source Charge	Q_{GS2}		4			1.3			
Gate to Drain Charge	Q_{GD}		12.2			4.5			
Switch Chg($Q_{GS2} + Q_{GD}$)*	Q_{SW}		18.4	24		5.8	7.0		
Output Charge*	Q_{OSS}		25	30		26	31		$V_{DS} = 16V, V_{GS} = 0$
Gate Resistance	R_G		1.5			1.9		Ω	
Turn-on Delay Time	$t_{d(on)}$		17			10		ns	$V_{DD} = 16V, I_D = 15A$ $V_{GS} = 5V$ Clamped Inductive Load
Rise Time	t_r		10			5			
Turn-off Delay Time	$t_{d(off)}$		39			19			
Fall Time	t_f		19			8			
Input Capacitance	C_{iss}	–	7300	–	–	1800	–	pF	$V_{DS} = 16V, V_{GS} = 0$
Output Capacitance	C_{oss}	–	900	–	–	900	–		
Reverse Transfer Capacitance	C_{rss}	–	350	–	–	60	–		

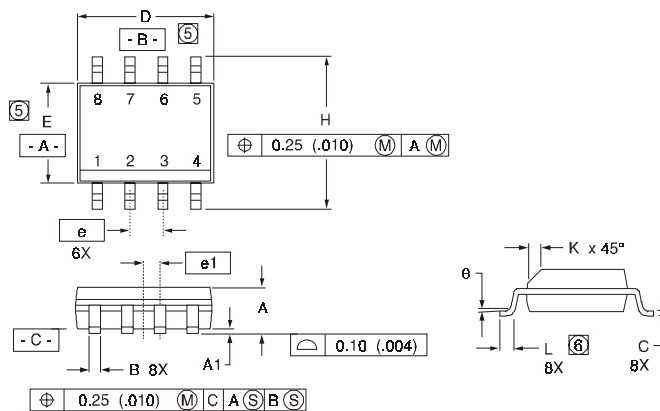
Source-Drain Rating & Characteristics

Parameter		Min	Typ	Max	Min	Typ	Max	Units	Conditions
Diode Forward Voltage*	V_{SD}			1.0			1.0	V	$I_S = 15A$ ②, $V_{GS} = 0V$
Reverse Recovery Charge④	Q_{rr}		94			82		nC	$di/dt \sim 700A/\mu s$ $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$
Reverse Recovery Charge (with Parallel Schottky)④	$Q_{rr(s)}$		87			74			$di/dt = 700A/\mu s$ (with 10BQ040) $V_{DS} = 16V, V_{GS} = 0V, I_S = 15A$

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- ③ When mounted on 1 inch square copper board, $t < 10$ sec.
- ④ Typ = measured - Q_{OSS}
- * Devices are 100% tested to these parameters.

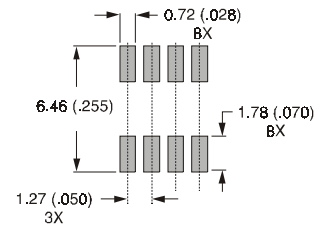
SO-8 Package Outline



NOTES:

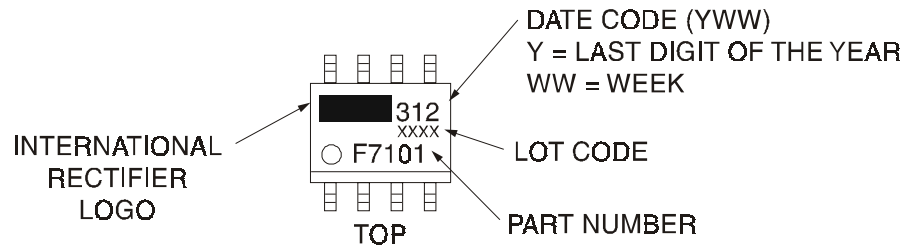
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS
MOLD PROTRUSIONS NOT TO EXCEED .025 (.006).
6. DIMENSIONS IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE..

RECOMMENDED FOOTPRINT



Part Marking Information

EXAMPLE: THIS IS AN IRF7101

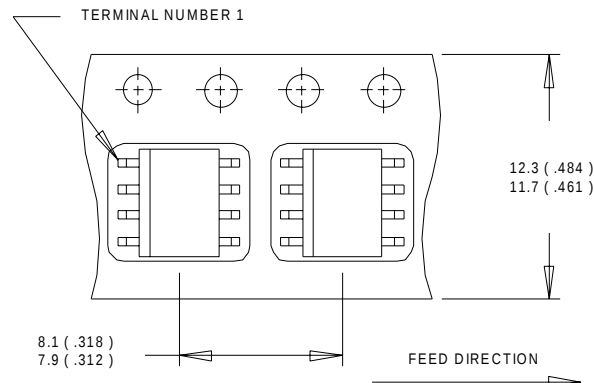


IRF7809/IRF7811

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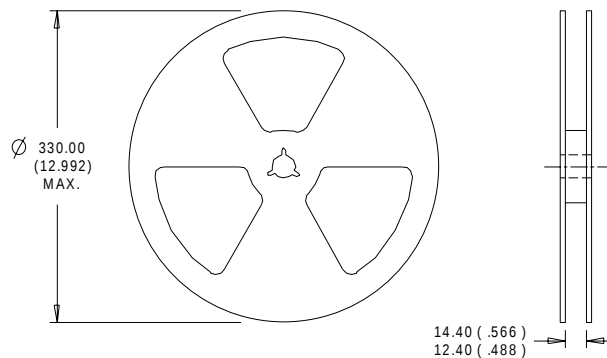
SO-8 Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

International
IR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 252-7105

IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T 3Z2, Tel: (905) 453 2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR JAPAN: K&H Bldg., 2F, 3-30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171-0021 Japan Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: 65 838 4630

IR TAIWAN : 16F, Suite B, 319, Sec.2, Tun Hwa South Road, Taipei 10673, Taiwan, R.O.C. Tel : 886-2-2739-4230

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